

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q76253

Naoki OYANAGI

Appln. No.: 10/560,745

Group Art Unit: 1792

Confirmation No.: 1691

Examiner: Felisa Carla HITESHEW

Filed: December 15, 2005

For: METHOD FOR GROWTH OF SILICON CARBIDE SINGLE CRYSTAL, SILICON
CARBIDE SEED CRYSTAL, AND SILICON CARBIDE SINGLE CRYSTAL

SUBMISSION OF SUBSTANCE OF INTERVIEW

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

As set forth in the Interview Summary of the Interview of August 21, 2008, which is attached to the Notice of Allowability, applicant's undersigned counsel authorized the Examiner to cancel non-elected claims 5-7, and to cancel claim 11, which was believed to recite the same subject matter as claim 10. In addition, applicant's undersigned counsel authorized the Examiner to amend claim 4 to recite that a crystal face of the seed crystal is inclined "by 4 to 45°" relative to the recited plane to further distinguish over U.S. Patent 5,958,132 to Takahashi et al.

Respectfully submitted,

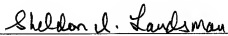
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Date: October 6, 2008


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